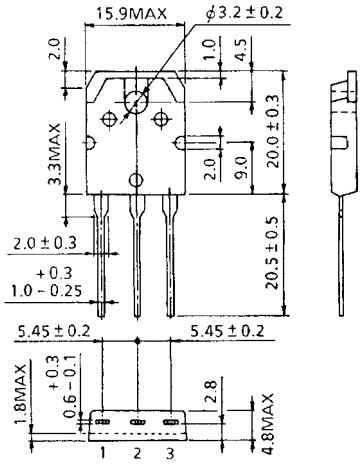
TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT10Q301

High Power Switching Applications
Motor Control Applications

- Third-generation IGBT
- Enhancement mode type
- High speed: t_f = 0.32 μs (max)
- Low saturation voltage: $V_{CE\ (sat)}$ = 2.7 V (max)
- FRD included between emitter and collector

Unit: mm



1. GATE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
JEITA	—
TOSHIBA	2-16C1C

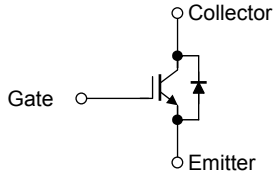
Weight: 4.6 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

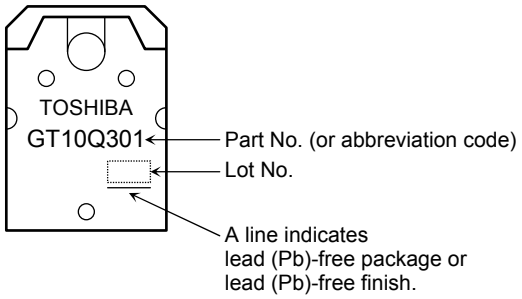
Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	1200	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C	10	A
	1 ms	I_{CP}	20	
Emitter-collector forward current	DC	I_F	10	A
	1 ms	I_{FM}	20	
Collector power dissipation (Tc = 25°C)		P_C	140	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit



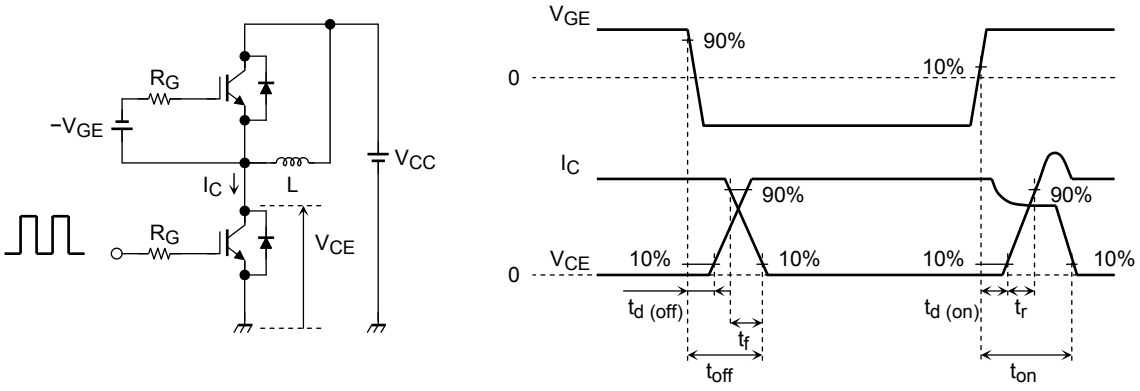
Marking



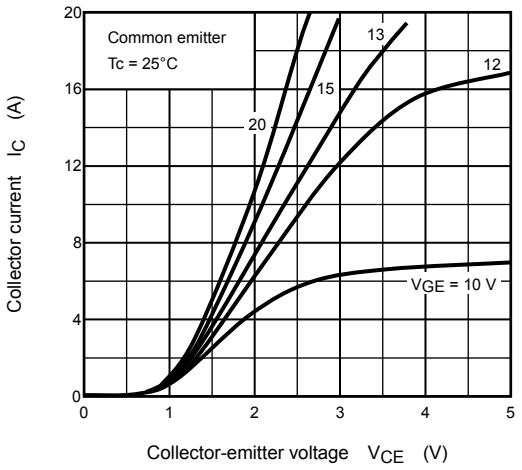
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	V_{GE} = ±20 V, V_{CE} = 0	—	—	±500	nA
Collector cut-off current		I_{CES}	V_{CE} = 1200 V, V_{GE} = 0	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE\ (OFF)}$	I_C = 1 mA, V_{CE} = 5 V	4.0	—	7.0	V
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 10 A, V_{GE} = 15 V	—	2.1	2.7	V
Input capacitance		C_{ies}	V_{CE} = 50 V, V_{GE} = 0, f = 1 MHz	—	600	—	pF
Switching time	Rise time	t_r	Inductive load V_{CC} = 600 V, I_C = 10 A V_{GG} = ±15 V, R_G = 75 Ω (Note)	—	0.07	—	μs
	Turn-on time	t_{on}		—	0.30	—	
	Fall time	t_f		—	0.16	0.32	
	Turn-off time	t_{off}		—	0.50	—	
Peak forward voltage		V_F	I_F = 10 A, V_{GE} = 0	—	—	3.0	V
Reverse recovery time		t_{rr}	I_F = 10 A, di/dt = −200 A/μs	—	—	350	ns
Thermal resistance (IGBT)		$R_{th\ (j\text{-}c)}$	—	—	—	0.89	°C/W
Thermal resistance (diode)		$R_{th\ (j\text{-}c)}$	—	—	—	1.79	°C/W

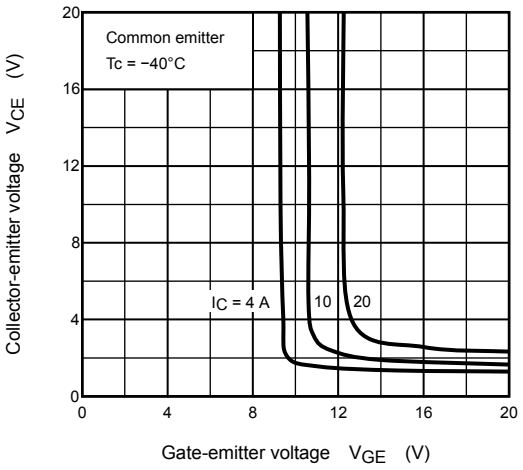
Note: Switching time measurement circuit and input/output waveforms



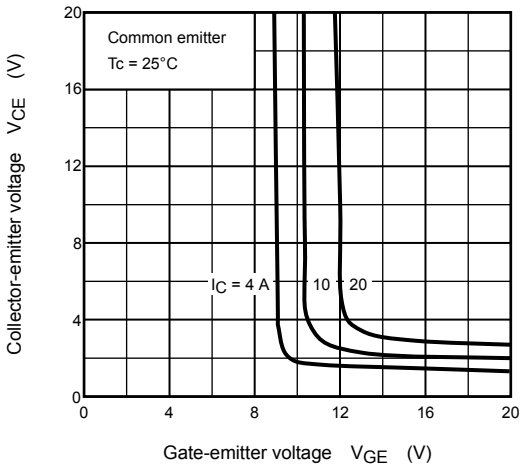
$I_C - V_{CE}$



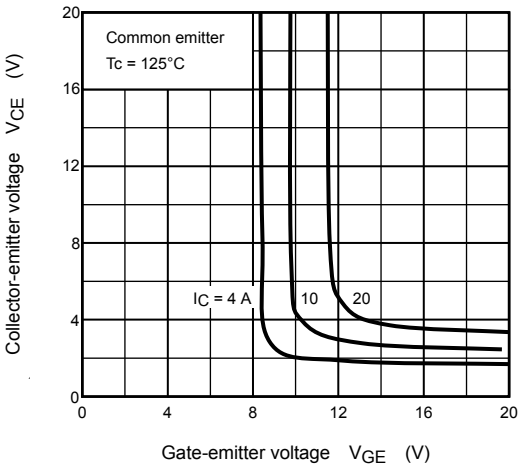
$V_{CE} - V_{GE}$



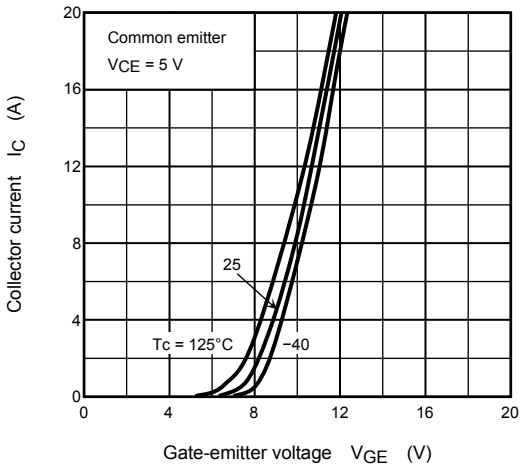
$V_{CE} - V_{GE}$



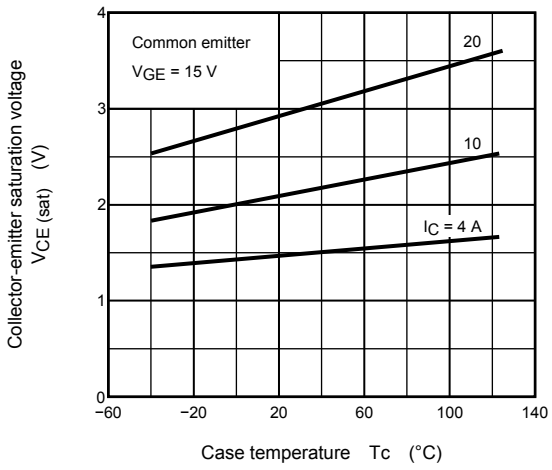
$V_{CE} - V_{GE}$



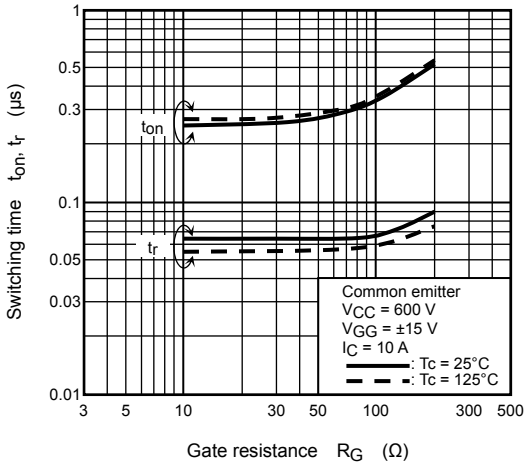
$I_C - V_{GE}$



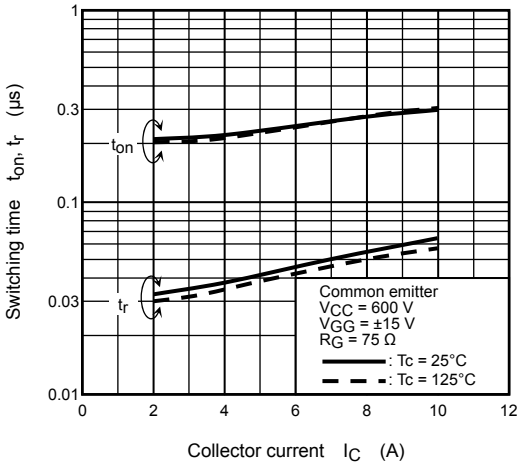
$V_{CE\ (sat)} - Tc$



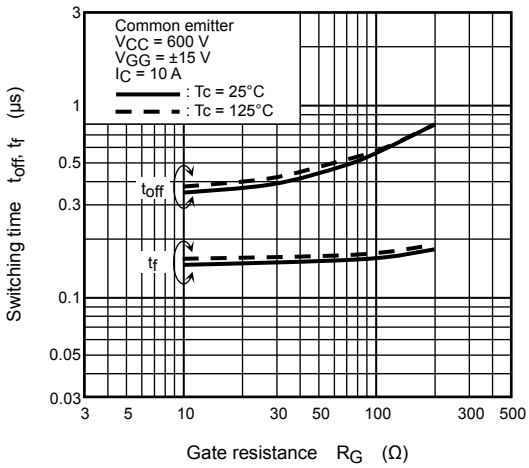
Switching Time t_{on}, t_r – R_G



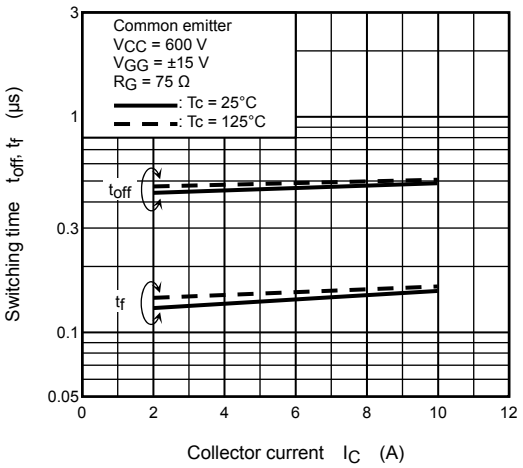
Switching Time t_{on}, t_r – I_C



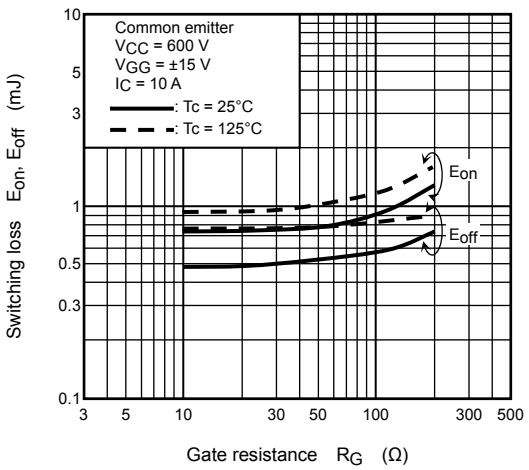
Switching Time t_{off}, t_f – R_G



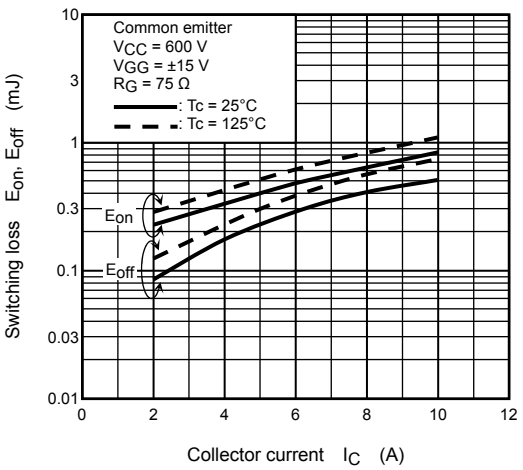
Switching Time t_{off}, t_f – I_C



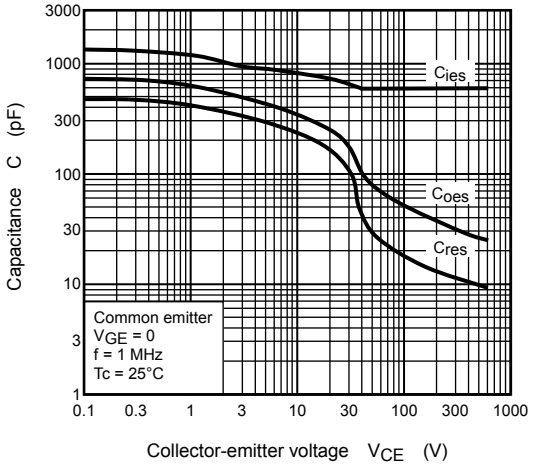
Switching Loss E_{on}, E_{off} – R_G



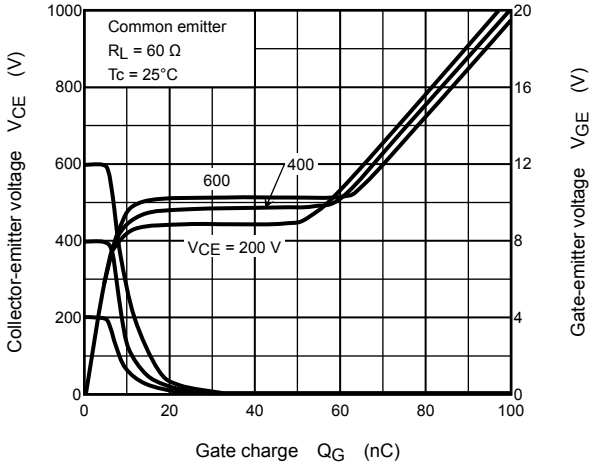
Switching Loss E_{on}, E_{off} – I_C



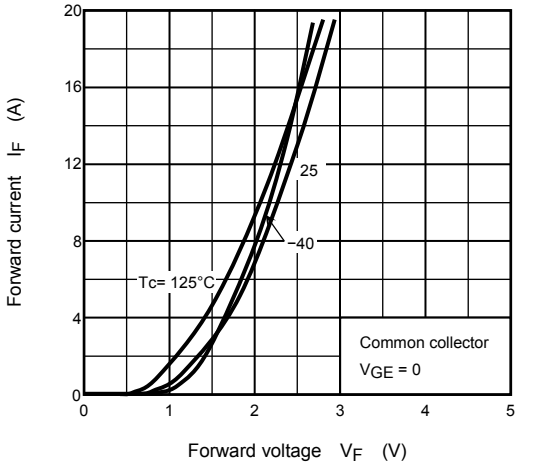
$C - V_{CE}$



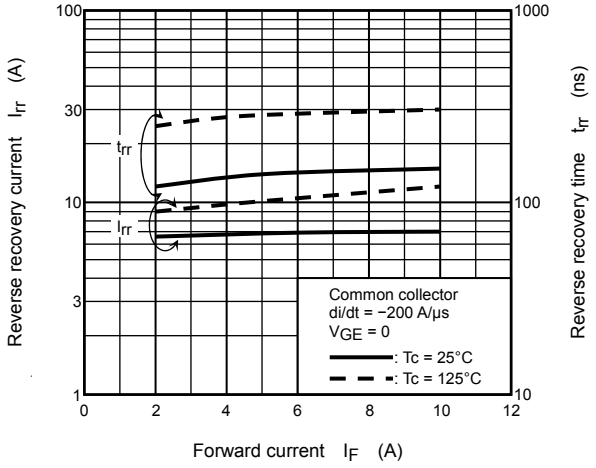
V_{CE}, $V_{GE} - Q_G$



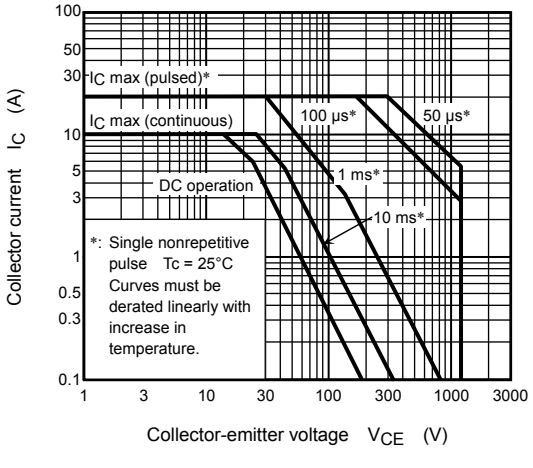
$I_F - V_F$



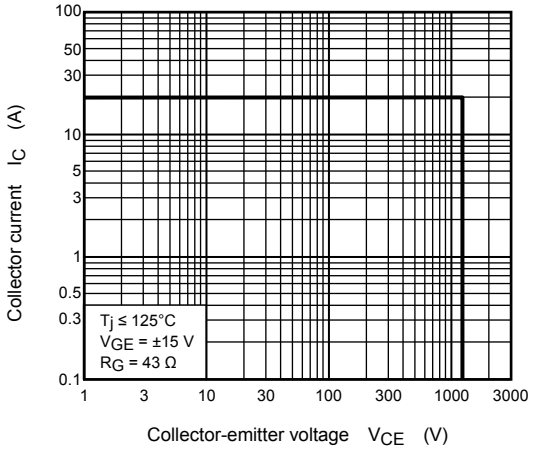
t_{rr}, $I_{rr} - I_F$

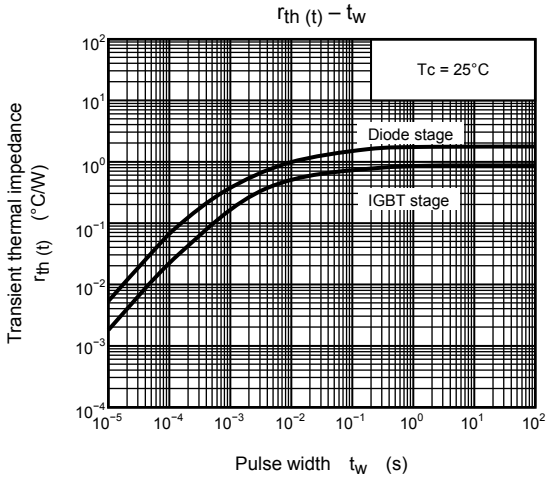


Safe Operating Area



Reverse Bias SOA




$r_{th\ (t)} - t_w$
Tc = 25°C
Diode stage
IGBT stage
Transient thermal impedance r_{th} (t) (°C/W)
Pulse width t_w (s)
10^{2}
10^{1}
10^{0}
10^{-1}
10^{-2}
10^{-3}
10^{-4}
10^{-5}
10^{-4}
10^{-3}
10^{-2}
10^{-1}
10^{0}
10^{1}
10^{2}

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20070701-EN

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